BAS40LT1

Preferred Device

Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

Features

WWW.DZSC.COM • Pb–Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	40	V
Forward Power Dissipation @ T _A = 25°C Derate above 25°C	P _F	225 1.8	mW mW/°C
Operating Junction and Storage Temperature Range	T _{J,} T _{stg}	-55 to +150	°C
Forward Continuous Current	١ _F	120	mA
$\begin{array}{ll} \mbox{Forward Surge Current} & t \leq 1 \ s \\ t \leq 10 \ ms \end{array}$	I _{FSM}	200 600	mA
Thermal Resistance Junction-to-Ambient	R _{θJA}	508 (Note 1) 311 (Note 2)	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-4 @ minimum pad. 2. FR-4 @ 1.0 x 1.0 in pad.



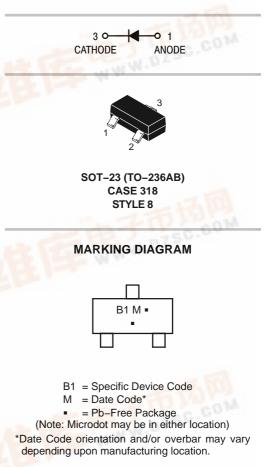
24小时加急出货

ON Semiconductor®

专业PCB打样工

http://onsemi.com

40 VOLTS SCHOTTKY BARRIER DIODES



ORDERING INFORMATION

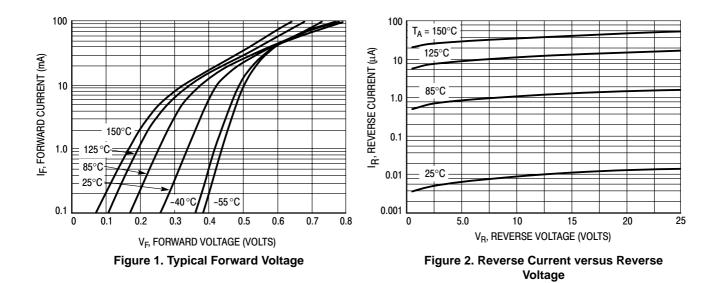
Device	Package	Shipping [†]
BAS40LT1	SOT-23	3000/Tape & Reel
BAS40LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

BAS40LT1

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage $(I_R = 10 \ \mu A)$	V _{(BR)R}	40	-	V
Total Capacitance ($V_R = 1.0 \text{ V}, f = 1.0 \text{ MHz}$)	CT	-	5.0	pF
Reverse Leakage (V _R = 25 V)	I _R	-	1.0	μAdc
Forward Voltage (I _F = 1.0 mAdc)	V _F	-	380	mVdc
Forward Voltage (I _F = 10 mAdc)	V _F	-	500	mVdc
Forward Voltage (I _F = 40 mAdc)	V _F	-	1.0	Vdc



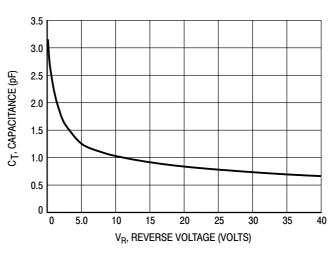
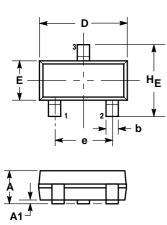


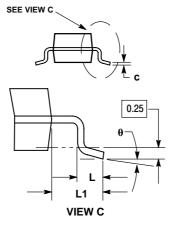
Figure 3. Typical Capacitance

BAS40LT1

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN**





- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD 3. THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL
- 318–01 THRU –07 AND –09 OBSOLETE, NEW STANDARD 318–08. 4

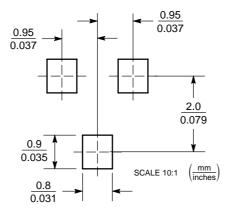
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 8:

PIN 1. ANODE

З

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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^{2.} NO CONNECTION CATHODE